



STGB18N40LZ
STGD18N40LZ

E_{AS} 180 mJ - 400 V - internally clamped IGBT

Features

- AEC Q101 compliant
- 180 mJ of avalanche energy @ $T_C = 150\text{ }^{\circ}\text{C}$,
 $L = 3\text{ mH}$
- ESD gate-emitter protection
- Gate-collector high voltage clamping
- Logic level gate drive
- Low saturation voltage
- High pulsed current capability
- Gate and gate-emitter resistor

Application

- Pencil coil electronic ignition driver

Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

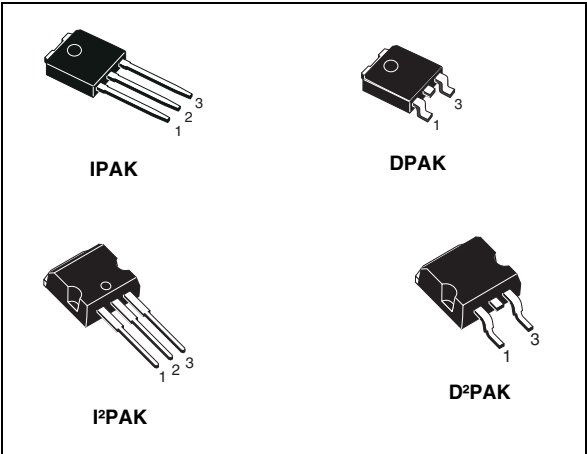


Figure 1. Internal schematic diagram

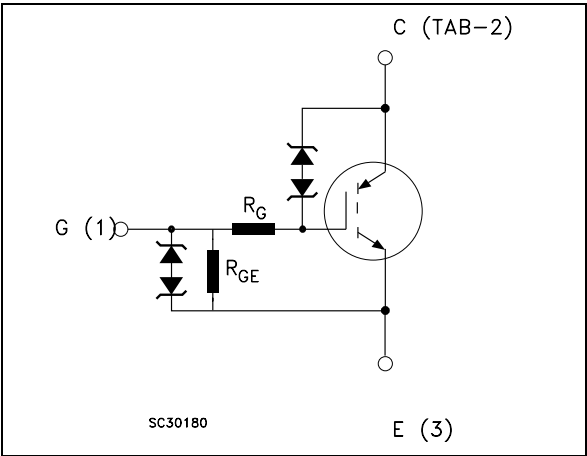


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGD18N40LZT4	GD18N40LZ	DPAK	Tape and reel
STGD18N40LZ-1	GD18N40LZ	IPAK	Tube
STGB18N40LZT4	GB18N40LZ	D²PAK	Tape and reel
STGB18N40LZ-1	GB18N40LZ	I²PAK	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		DPAK IPAK	D ² PAK I ² PAK	
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	V _{CES(clamped)}		V
V _{ECS}	Emitter collector voltage (V _{GE} = 0)	20		V
I _C ⁽¹⁾	Collector current (continuous) at T _C = 100 °C	25	30	A
I _{CP} ⁽²⁾	Pulsed collector current	40		A
V _{GE}	Gate-emitter voltage	V _{GE(clamped)}		V
P _{TOT}	Total dissipation at T _C = 25 °C	125	150	W
E _{AS}	Single pulse energy T _C = 25 °C, L = 3 mH, R _G = 1 KΩ	300		mJ
E _{AS}	Single pulse energy T _C = 150 °C, L = 3 mH, R _G = 1 KΩ	180		mJ
E _{SD}	Human body model, R = 1550 Ω, C = 100 pF	8		kV
	Machine model, R = 0, C = 100 pF	800		V
	Charged device model	2		kV
T _{stg}	Storage temperature	- 55 to 175		°C
T _j	Operating junction temperature			

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

2. Pulse width limited by max. junction temperature allowed

Table 3. Thermal resistance

Symbol	Parameter	Value		Unit
		DPAK IPAK	D ² PAK I ² PAK	
R _{thj-case}	Thermal resistance junction-case max	1.2	1	°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	65	62.5	°C/W

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{CES(\text{clamped})}$	Collector emitter clamped voltage ($V_{GE} = 0$)	$I_C = 2 \text{ mA}$, $R_G = 1 \text{ k}\Omega$ $T_C = -40^{\circ}\text{C}$ to 150°C	370	400	430	V
$V_{(BR)ECS}$	Emitter collector break-down voltage ($V_{GE} = 0$)	$I_C = 75 \text{ mA}$	20	28		V
$V_{GE(\text{clamped})}$	Gate emitter clamped voltage	$I_G = \pm 2 \text{ mA}$	12		16	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 15 \text{ V}$, $T_C = 150^{\circ}\text{C}$			10	μA
		$V_{CE} = 200 \text{ V}$, $T_C = 150^{\circ}\text{C}$			100	μA
I_{GES}	Gate cut-off current ($V_{CE} = 0$)	$V_{GE} = \pm 10 \text{ V}$	450	625	830	μA
R_{GE}	Gate emitter resistance		12	16	22	$\text{K}\Omega$
R_G	Gate resistance			1.6		$\text{K}\Omega$
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE} = 12 \text{ V}$, $I_C = 1 \text{ mA}$, $T_C = -40^{\circ}\text{C}$	1.4			V
		$V_{CE} = 12 \text{ V}$, $I_C = 1 \text{ mA}$	1.2	1.6	2.3	V
		$V_{CE} = 12 \text{ V}$, $I_C = 1 \text{ mA}$, $T_C = 150^{\circ}\text{C}$	0.7			V
V_{GEP}	Gate emitter plateau voltage	$V_{CE} = 12 \text{ V}$, $I_C = 10 \text{ A}$		2.9		V
$V_{CE(\text{sat})}$	Collector emitter saturation voltage	$V_{GE} = 4.5 \text{ V}$, $I_C = 10 \text{ A}$		1.35	1.7	V
		$V_{GE} = 4.5 \text{ V}$, $I_C = 10 \text{ A}$, $T_C = 150^{\circ}\text{C}$		1.30		V
		$V_{GE} = 3.8 \text{ V}$, $I_C = 6 \text{ A}$		1.30		V

Table 5. Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$		490		pF
C_{oes}	Output capacitance			90		pF
C_{res}	Reverse transfer capacitance			6.5		pF
Q_g	Gate charge	$V_{CE} = 280\text{ V}$, $I_C = 10\text{ A}$, $V_{GE} = 5\text{ V}$		23		nC

Table 6. Switching on/off

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Resistive load Turn-on delay time	$V_{CC} = 14\text{ V}$, $I_C = 10\text{ A}$ $R_G = 1\text{ k}\Omega$, $V_{GE} = 5\text{ V}$		1		μs
	Rise time			5.8		μs
$t_{d(on)}$ t_r	Resistive load Turn-on delay time	$V_{CC} = 14\text{ V}$, $I_C = 10\text{ A}$ $R_G = 1\text{ k}\Omega$, $V_{GE} = 5\text{ V}$, $T_C = 150\text{ }^\circ\text{C}$		1		μs
	Rise time			5.9		μs
$t_{d(off)}$ t_f dv/dt	Inductive load Turn-off delay time	$V_{CC} = 300\text{ V}$, $L = 1\text{ mH}$ $R_G = 1\text{ k}\Omega$, $V_{GE} = 5\text{ V}$		14		μs
	Fall time			6.7		μs
	Turn-off voltage slope			90		V/ μs
$t_{d(off)}$ t_f dv/dt	Inductive load Turn-off delay time	$V_{CC} = 300\text{ V}$, $L = 1\text{ mH}$ $R_G = 1\text{ k}\Omega$, $V_{GE} = 5\text{ V}$, $T_C = 150\text{ }^\circ\text{C}$		15		μs
	Fall time			9.8		μs
	Turn-off voltage slope			80		V/ μs

2.1 Electrical characteristics (curves)

Figure 2. Collector-emitter voltage vs temperature

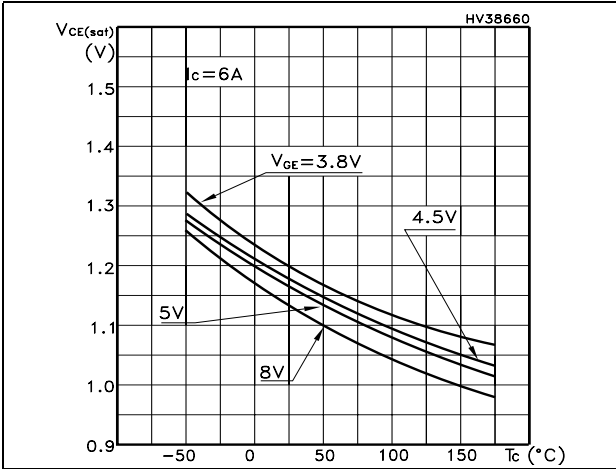


Figure 3. Collector-emitter voltage vs temperature

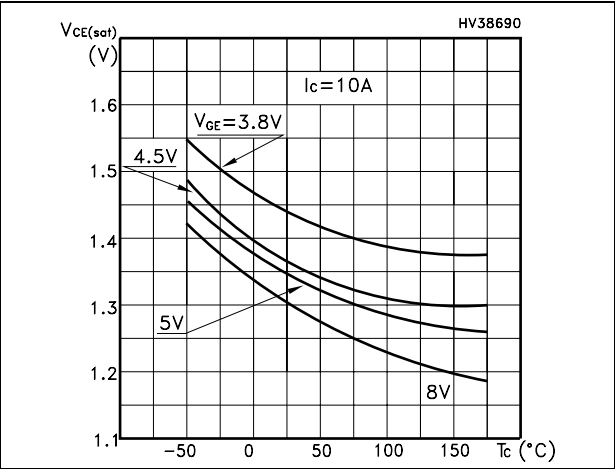


Figure 4. Collector-emitter voltage vs temperature

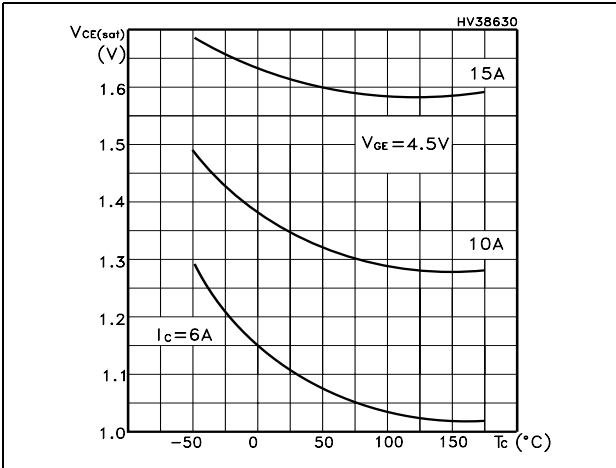


Figure 5. Self clamped inductive switch

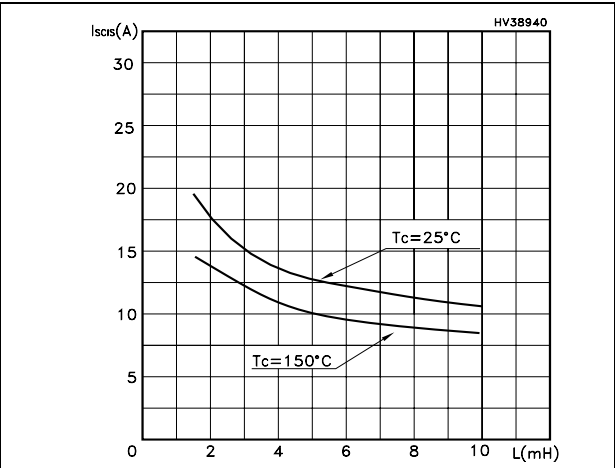


Figure 6. Collector current vs collector emitter voltage @ 25 °C

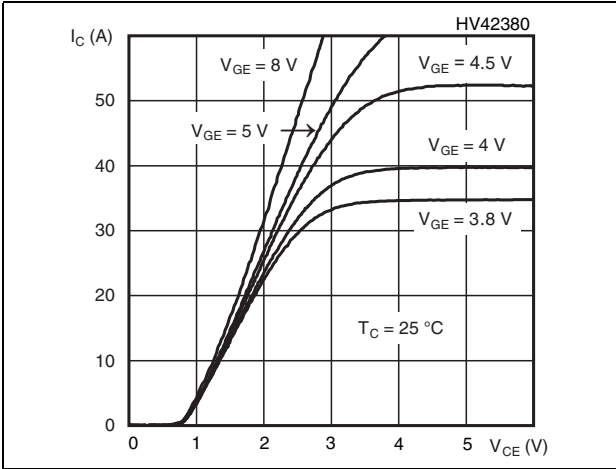


Figure 7. Collector current vs collector emitter voltage @ -40 °C

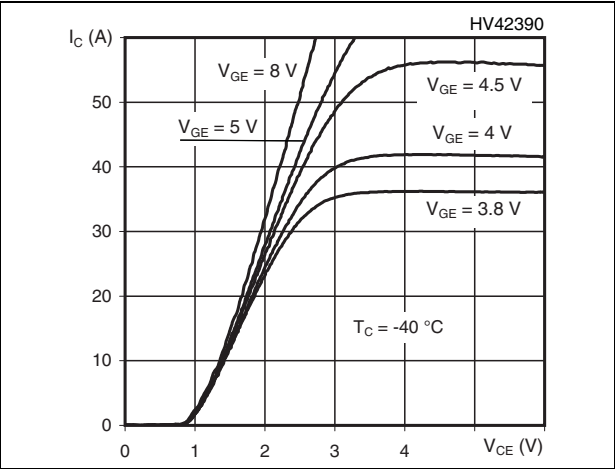


Figure 8. Collector current vs collector emitter voltage @ 175 °C

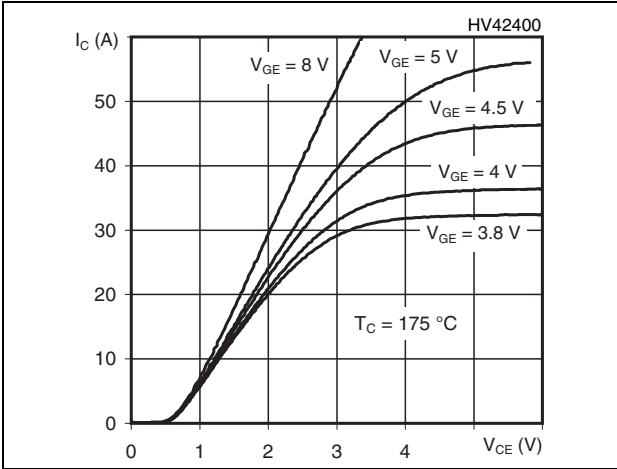


Figure 9. Transfer characteristics

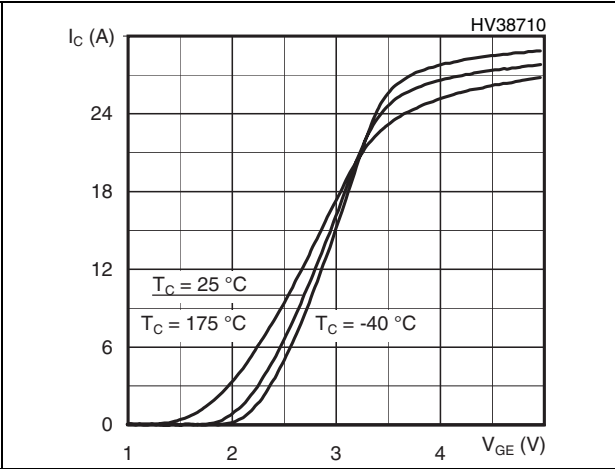


Figure 10. Collector emitter leakage current vs. temperature

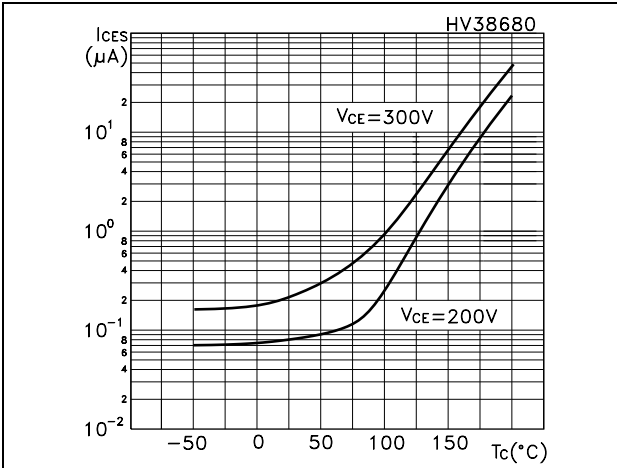


Figure 11. Normalized collector emitter breakdown voltage vs temperature

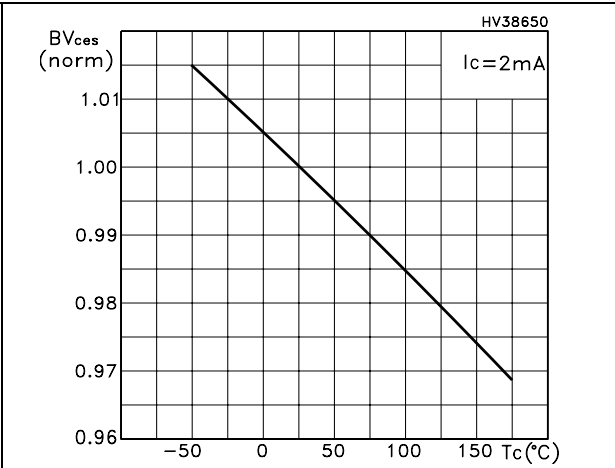


Figure 12. Normalized gate threshold voltage vs temperature

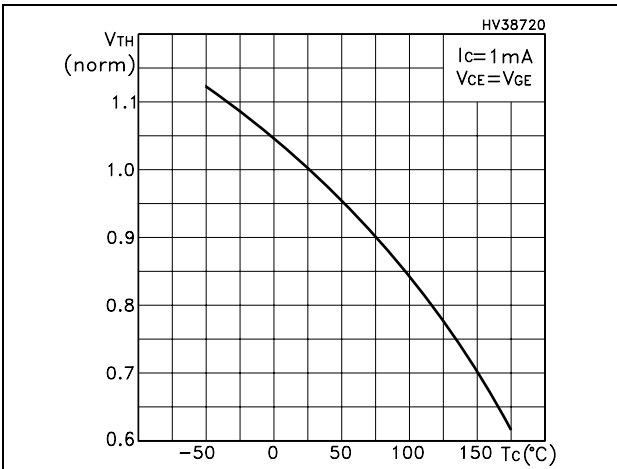


Figure 13. Normalized collector emitter voltage vs temperature

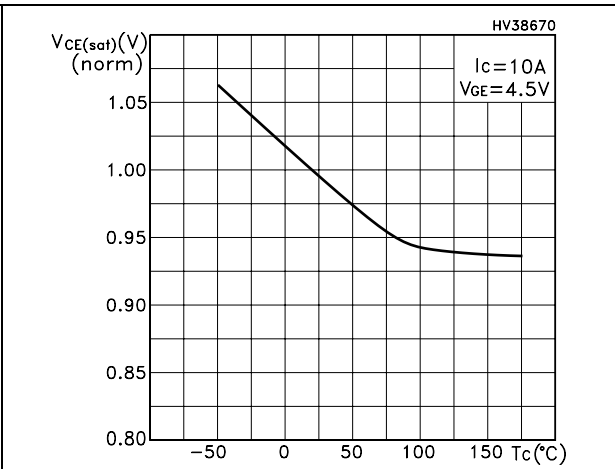


Figure 14. Thermal impedance for D²PAK / I²PAK

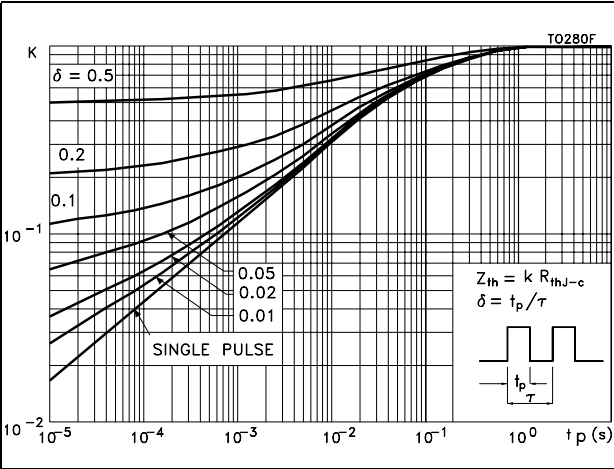
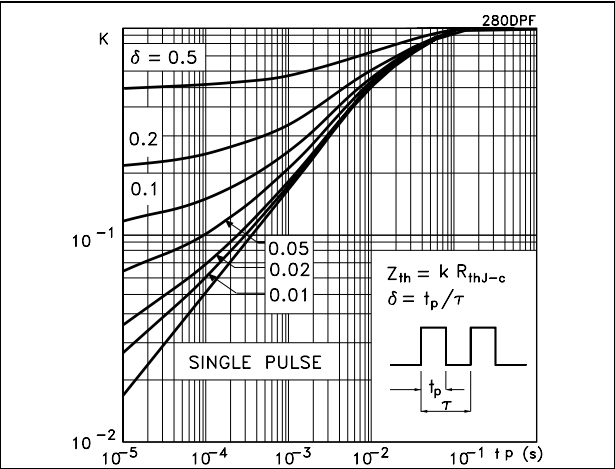


Figure 15. Thermal impedance for DPAK / IPAK



3 Test circuits

Figure 16. Test circuit for inductive load switching

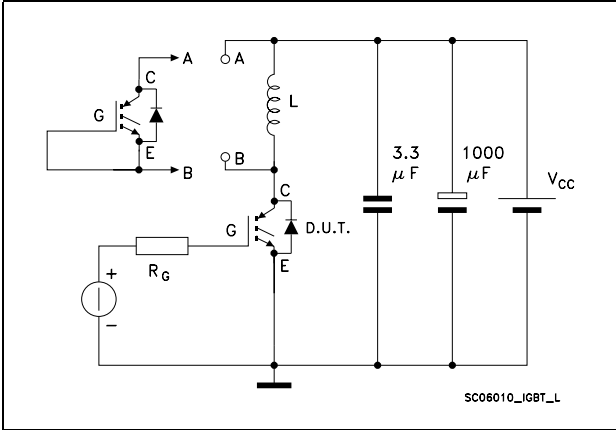


Figure 17. Gate charge test circuit

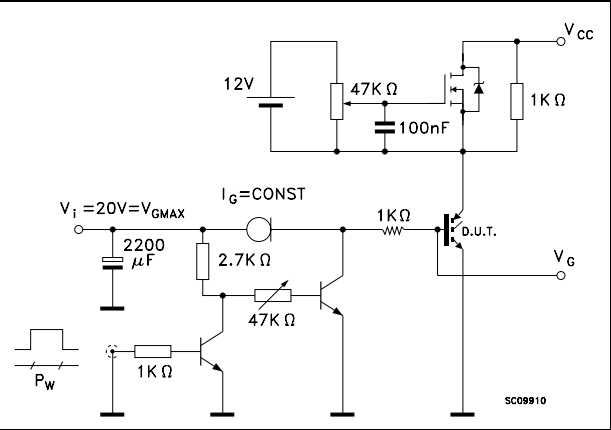


Figure 18. Switching waveform

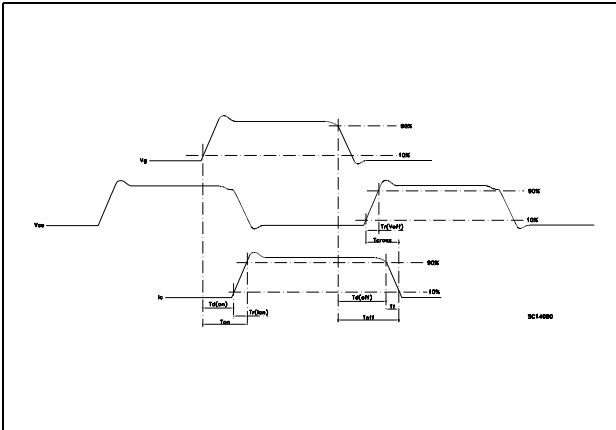
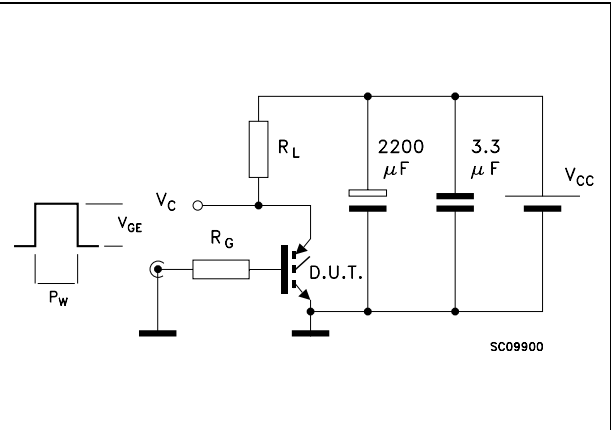


Figure 19. Test circuit for resistive load switching

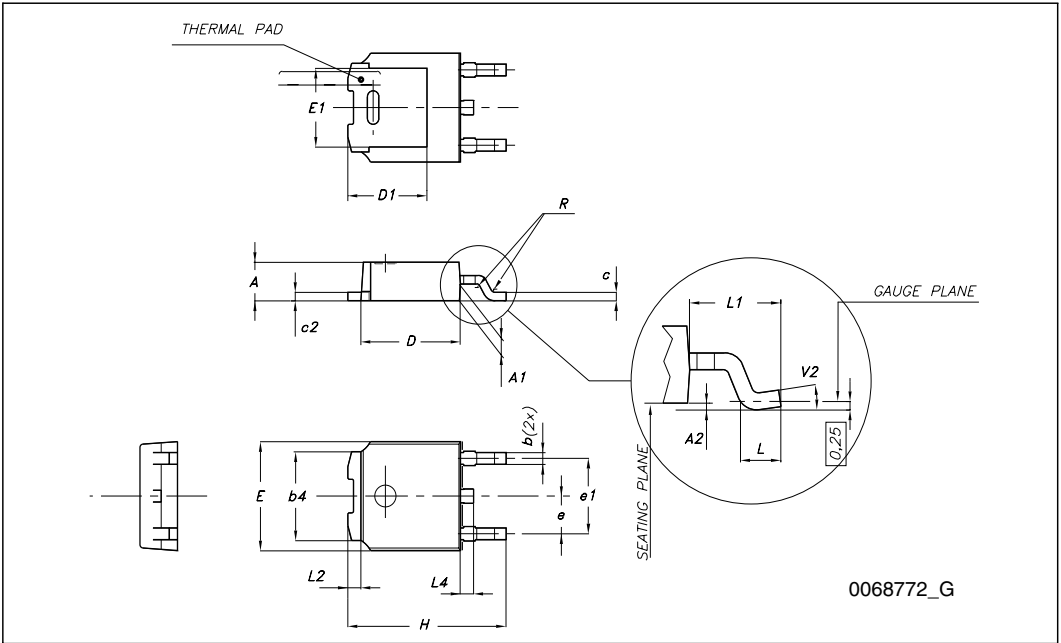


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

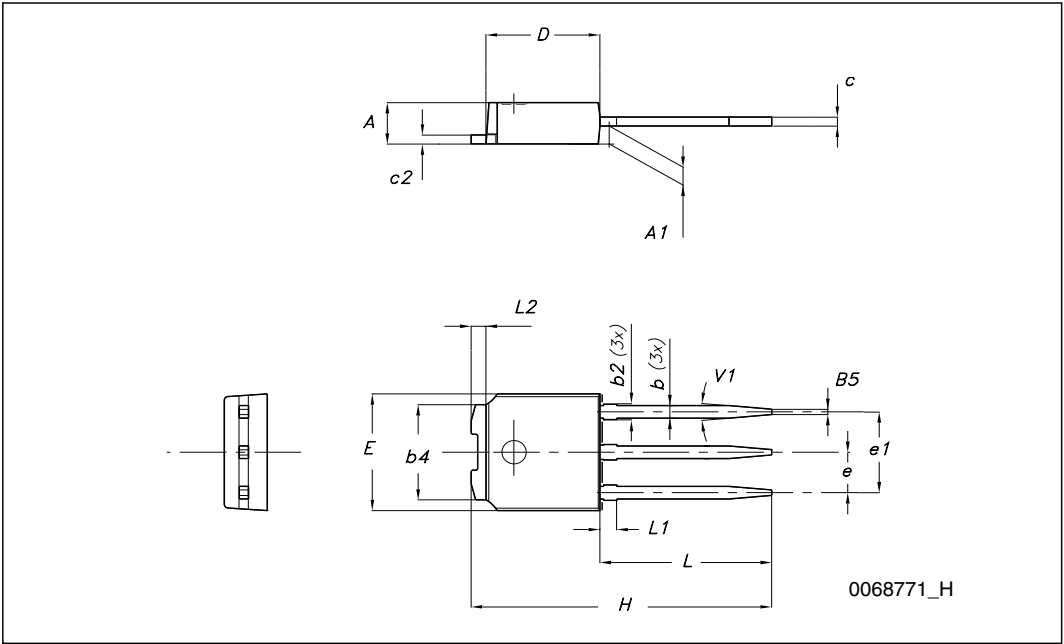
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



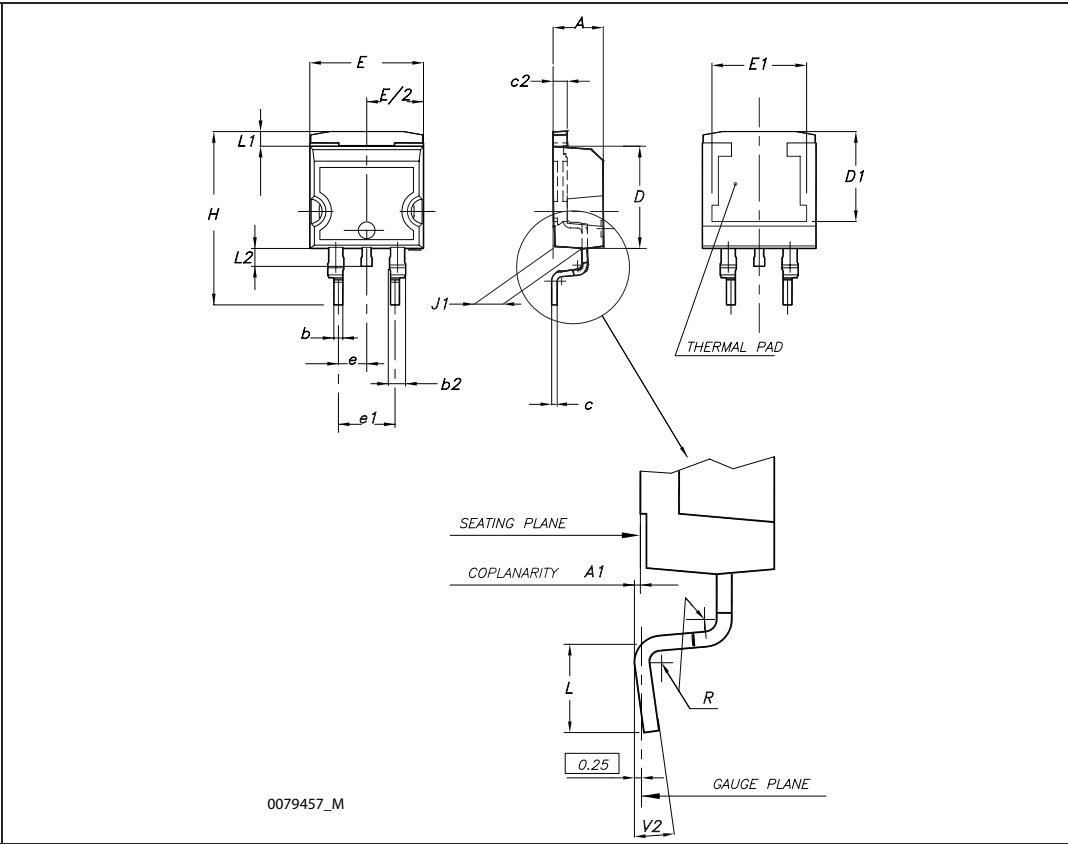
TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



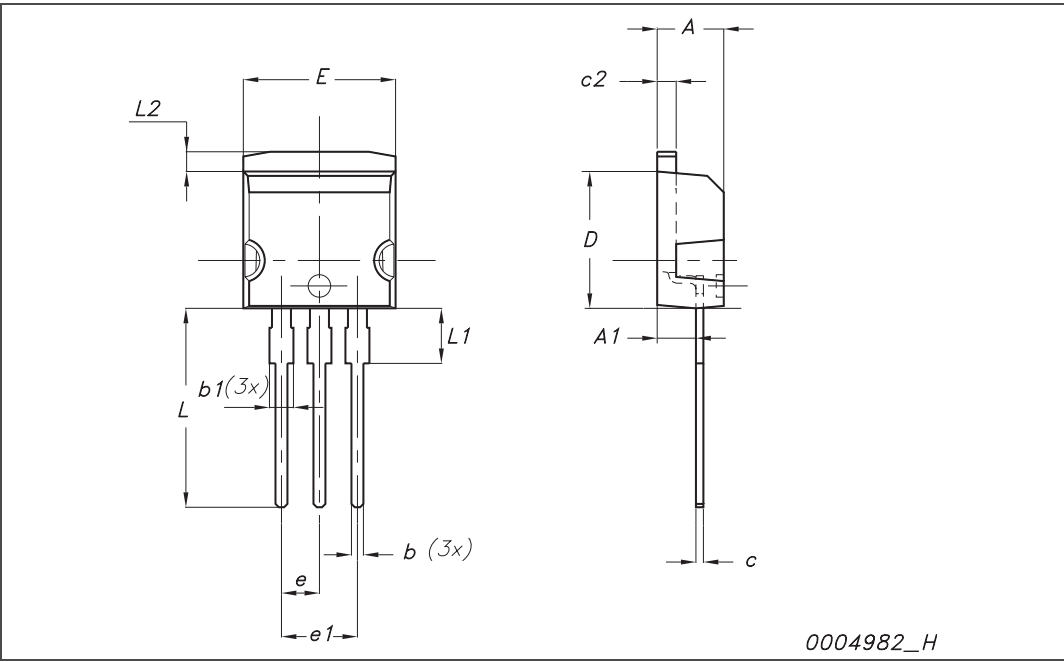
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



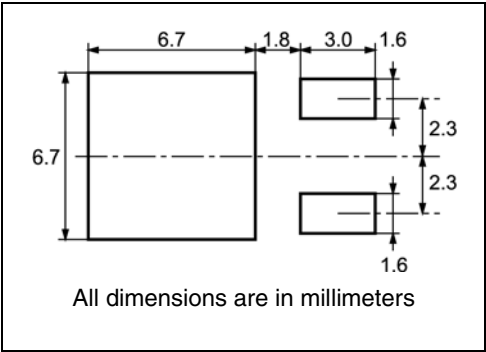
I²PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055

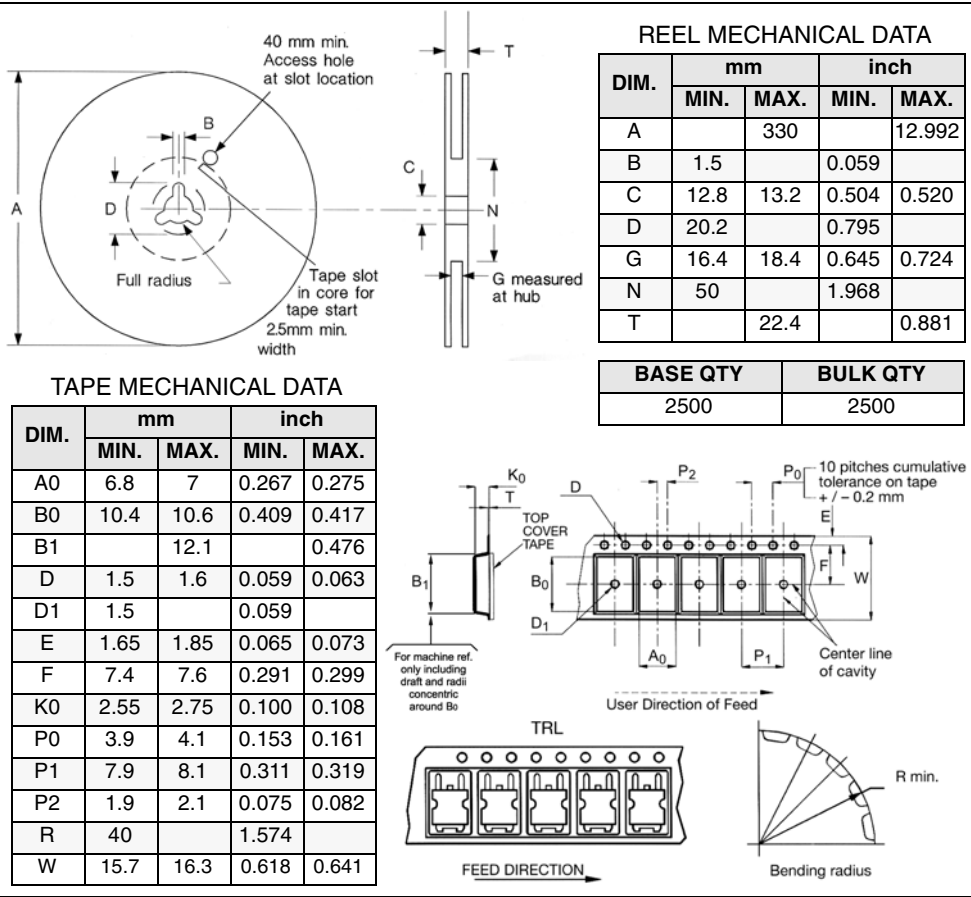


5 Packaging mechanical data

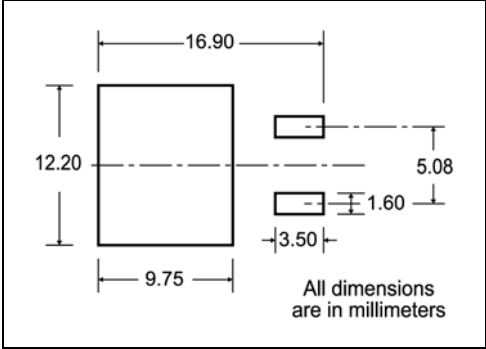
DPAK FOOTPRINT



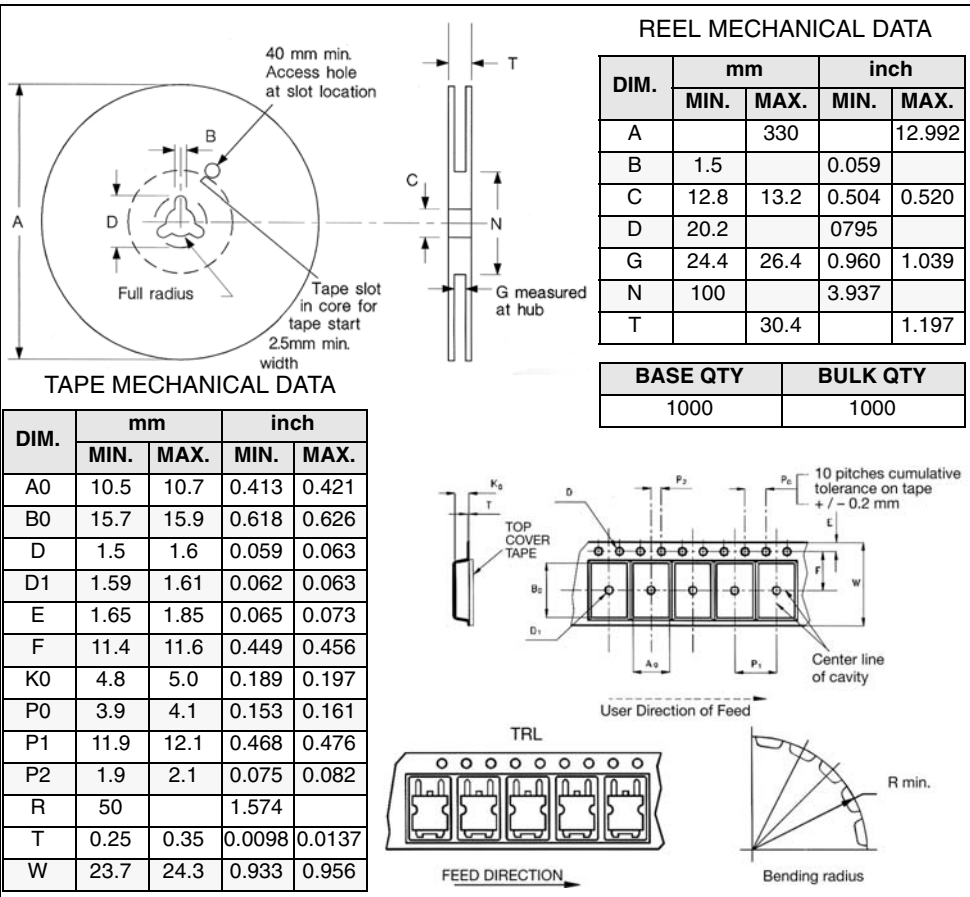
TAPE AND REEL SHIPMENT



D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 7. Document revision history

Date	Revision	Changes
18-Jan-2008	1	Initial release.
07-Mar-2008	2	Modified Figure 7 , Figure 8 , Figure 10 .

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